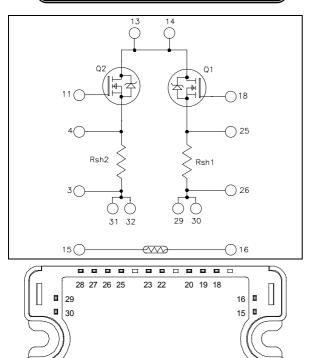


Linear MOSFET Power Module



Pins 13/14 ; 29/30 ; 31/32 must be shorted together

Absolute maximum ratings (per leg)

1 31

Symbol	Parameter		Max ratings	Unit
V _{DSS}	Drain - Source Breakdown Voltage		600	V
т	Continuous Drain Current	$T_c = 25^{\circ}C$	45*	
ID	Continuous Drain Current	$T_c = 80^{\circ}C$	33*	А
I _{DM}	V_{DSS} Drain - Source Breakdown Voltage I_D Continuous Drain Current I_{DM} Pulsed Drain current V_{GS} Gate - Source Voltage $DSon$ Drain - Source ON Resistance P_D Maximum Power Dissipation \mathbf{O} I_{AR} Avalanche current (repetitive and non repetitive) E_{AR} Repetitive Avalanche Energy		172	
V _{GS}	Gate - Source Voltage		± 30	V
R _{DSon}			150	mΩ
P _D	Maximum Power Dissipation $T_c = 25^{\circ}C$		568	W
I _{AR}	Avalanche current (repetitive and non repetitive)		45	А
E _{AR}	Repetitive Avalanche Energy		50	mI
E _{AS}	Single Pulse Avalanche Energy		3000	mJ

14

* Output current must be limited to 31A @ $T_c=25$ °C and 22A @ $T_c=80$ °C to not exceed the shunt specification. • In saturation mode

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

APTML602U12R020T3AG

$V_{DSS} = 600V$ $R_{DSon} = 125m\Omega \text{ typ } @ \text{ Tj} = 25^{\circ}C$ $I_{D} = 45A^{*} @ \text{ Tc} = 25^{\circ}C$

Application

• Electronic load dedicated to power supplies and battery discharge testing

Features

- Linear MOSFET
- Very low stray inductance
- Internal thermistor for temperature monitoring
- High level of integration
- AlN substrate for improved thermal performance

Benefits

- Direct mounting to heatsink (isolated package)
- easy series and parallels combinations for power and voltage improvements
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

1 - 4



Microsemi APTML602U12R020T3AG

All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics (per leg)

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit	
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 600V$; $V_{GS} = 0V$ $T_j = 25^{\circ}C$			25		
		$V_{DS} = 480V$; $V_{GS} = 0V$ $T_j = 125^{\circ}C$			250	μA	
R _{DS(on)}	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 22.5A$		125	150	mΩ	
V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 2.5 \text{mA}$	2		4	V	
I _{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30 \text{ V}$			±100	nA	

Dynamic Characteristics (per leg)

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
C _{iss}	Input Capacitance	$V_{GS} = 0V$		7600		
Coss	Output Capacitance	$V_{DS} = 25V$		1280		pF
C _{rss}	Reverse Transfer Capacitance	f = 1 MHz		620		

Shunt Electrical Characteristics (per leg)

Symbol	Characteristic		Min	Тур	Max	Unit
R _{sh}	Resistance value			20		mΩ
T _{sh}	Tolerance			2		%
P _{sh}	Load capacity $\frac{T_{C}=25^{\circ}C}{T_{C}=80^{\circ}C}$	25°C		20	W	
r _{sh}		80°C		10	vv	
T.	Current capacity	$T_{C} = 2$	25°C		31	٨
1 _{sh}	Current capacity	$T_{C}=$	80°C		22	А

Temperature sensor PTC

Symbol	Characteristic		Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C		1980		2020	Ω
R_{100}/R_{25}	Resistance ratio	Tamb=100°C & 25°C	1.676	1.696	1.716	
R_{-55}/R_{25}	Resistance ratio	Tamb=-55°C & 25°C	0.48	0.49	0.50	
В	Temperature coefficient			7900		ppm/K

Thermal and package characteristics

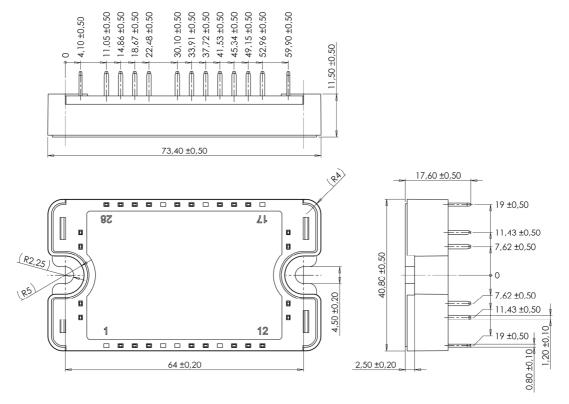
Symbol	Characteristic			Min	Тур	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance	MOSFET (per leg)			0.22	°C/W
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T _J	Operating junction temperature range			-40		150	
T _{STG}	Storage Temperature Range			-40		125	°C
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight					110	g

APTML602U12R020T3AG - Rev 2 October, 2012

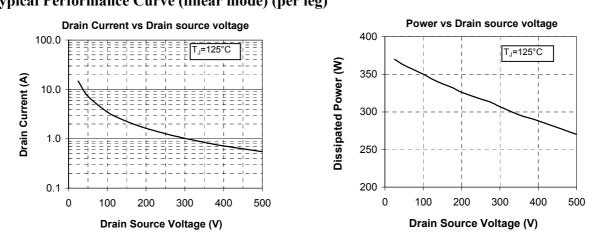
www.microsemi.com



SP3 Package outline (dimensions in mm)



See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com



Typical Performance Curve (linear mode) (per leg)



APTML602U12R020T3AG

DISCLAIMER

The information contained in the document (unless it is publicly available on the Web without access restrictions) is PROPRIETARY AND CONFIDENTIAL information of Microsemi and cannot be copied, published, uploaded, posted, transmitted, distributed or disclosed or used without the express duly signed written consent of Microsemi. If the recipient of this document has entered into a disclosure agreement with Microsemi, then the terms of such Agreement will also apply. This document and the information contained herein may not be modified, by any person other than authorized personnel of Microsemi. No license under any patent, copyright, trade secret or other intellectual property right is granted to or conferred upon you by disclosure or delivery of the information, either expressly, by implication, inducement, estoppels or otherwise. Any license under such intellectual property rights must be approved by Microsemi in writing signed by an officer of Microsemi.

Microsemi reserves the right to change the configuration, functionality and performance of its products at anytime without any notice. This product has been subject to limited testing and should not be used in conjunction with lifesupport or other mission-critical equipment or applications. Microsemi assumes no liability whatsoever, and Microsemi disclaims any express or implied warranty, relating to sale and/or use of Microsemi products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright or other intellectual property right. Any performance specifications believed to be reliable but are not verified and customer or user must conduct and complete all performance and other testing of this product as well as any user or customers final application. User or customer shall not rely on any data and performance specifications or parameters provided by Microsemi. It is the customer's and user's responsibility to independently determine suitability of any Microsemi product and to test and verify the same. The information contained herein is provided "AS IS, WHERE IS" and with all faults, and the entire risk associated with such information is entirely with the User. Microsemi specifically disclaims any liability of any kind including for consequential, incidental and punitive damages as well as lost profit. The product is subject to other terms and conditions which can be located on the web at http://www.microsemi.com/legal/tnc.asp

Life Support Application

Seller's Products are not designed, intended, or authorized for use as components in systems intended for space, aviation, surgical implant into the body, in other applications intended to support or sustain life, or for any other application in which the failure of the Seller's Product could create a situation where personal injury, death or property damage or loss may occur (collectively "Life Support Applications").

Buyer agrees not to use Products in any Life Support Applications and to the extent it does it shall conduct extensive testing of the Product in such applications and further agrees to indemnify and hold Seller, and its officers, employees, subsidiaries, affiliates, agents, sales representatives and distributors harmless against all claims, costs, damages and expenses, and attorneys' fees and costs arising, directly or directly, out of any claims of personal injury, death, damage or otherwise associated with the use of the goods in Life Support Applications, even if such claim includes allegations that Seller was negligent regarding the design or manufacture of the goods.

Buyer must notify Seller in writing before using Seller's Products in Life Support Applications. Seller will study with Buyer alternative solutions to meet Buyer application specification based on Sellers sales conditions applicable for the new proposed specific part.